

Vishay Semiconductors

AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 105 A



ADD-A-PAK

PRIMARY CHARACTERISTICS						
I _{T(AV)}	105 A					
Туре	Modules - thyristor, standard					
Package	AAP Gen 7 (TO-240AA)					

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- High voltage
- Industrial standard package
- UL approved file E78996
- · Low thermal resistance
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _{T(AV)}	85 °C	105					
I _{T(RMS)}		165	А				
I _{TSM}	50 Hz	2000	A				
	60 Hz	2094					
l ² t	50 Hz	20	kA ² s				
1-1	60 Hz	18.26	KA-S				
l²√t		200	kA²√s				
V _{RRM}	Range	400 to 1600	V				
T _{Stg}		-40 to +130	°C				
TJ		-40 to +130	°C				





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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 130 °C mA			
	04	400	500	400				
VS-VSK.105	08	800	900	800	15			
12		1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	٦	EST CONDITIO	VALUES	UNITS	
Maximum average on-state current	I _{T(AV)}	180° conductio $T_C = 85 \ ^{\circ}C$	180° conduction, half sine wave, $T_{\rm C}$ = 85 °C		105	А
Maximum continuous RMS on-state current	1	DC			165	
Maximum continuous AMS on-state current	I _{T(RMS)}	T _C			78	°C
		t = 10 ms	No voltage	Sinusoidal	2000	
Maximum peak, one-cycle non-repetitive		t = 8.3 ms	reapplied	half wave,	2094	•
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	initial T _J =	1682	A
		t = 8.3 ms	reapplied	T _J maximum	1760	
		t = 10 ms	No voltage		20	
1 2. <i>c</i> · · ·	l ² t	t = 8.3 ms	reapplied	Initial T _J = T _J maximum	18.26	kA ² s
Maximum I ² t for fusing		t = 10 ms	100 % V _{BBM}		14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum $I^2 \sqrt{t}$ for fusing	l²√t (1)	t = 0.1 ms to 10 ms, no voltage reapplied T ₁ = T ₁ maximum			200	kA²√s
Martin and a fill and all all all as	V _{T(TO)} ⁽²⁾	Low level ⁽³⁾	$T_J = T_J maximum$		0.98	
Maximum value of threshold voltage		High level ⁽⁴⁾			1.12	V
Maximum value of on-state		Low level ⁽³⁾			2.7	
slope resistance	r _t ⁽²⁾	High level ⁽⁴⁾	$T_J = T_J maxin$	num	2.34	mΩ
Maximum on-state voltage drop	V _{TM}	$I_{TM} = \pi \times I_{T(AV)}$	T _J = 25 °C		1.8	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$\begin{split} T_J &= 25 \ ^{\circ}C, \ from \ 0.67 \ V_{DRM}, \\ I_{TM} &= \pi \ x \ I_{T(AV)}, \ I_g &= 500 \ mA, \ t_r < 0.5 \ \mu s, \ t_p > 6 \ \mu s \end{split}$			150	A/µs
Maximum holding current	I _H	$T_J = 25 \text{ °C}$, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	١L	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400	

Notes

⁽¹⁾ I²t for time $t_x = I^2 \sqrt{t} x \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} x I_{T(AV)} + r_t x (I_{T(RMS)})^2$

⁽³⁾ 16.7 % x π x I_{AV} < I < π x I_{AV}

(4) $I > \pi x I_{AV}$



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TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			12	W
Maximum average gate power	P _{G(AV)}			3.0	vv
Maximum peak gate current	I _{GM}			3.0	А
Maximum peak negative gate voltage	- V _{GM}			10	
		T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5	
		T _J = 125 °C		1.7	
		T _J = - 40 °C		270	mA
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	
		T _J = 125 °C		80	
Maximum gate voltage that will not trigger	V _{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V
Maximum gate current that will not trigger	I _{GD}	T_J = 125 °C, rated V _{DR}	6	mA	

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 130 °C, gate open circuit	20	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 130$ °C, linear to 0.67 V_{DRM}	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to 130	°C		
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.22	°C/W		
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	0/11		
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm		
	busbar		3 hours to allow for the spread of the compound.	3	INITI		
Approximate weight				75	g		
				2.7	oz.		
Case style			JEDEC®	AAP Gen 7	(TO-240AA)		

DEVICES	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				UNITS	
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.105	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

- Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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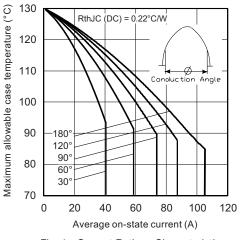
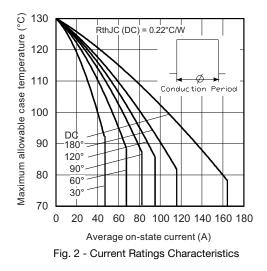


Fig. 1 - Current Ratings Characteristics



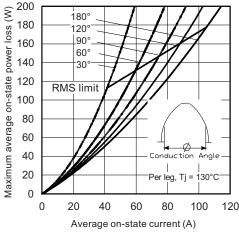
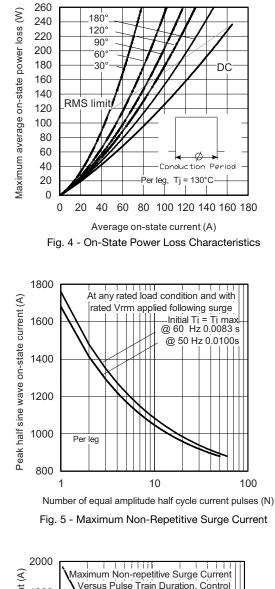


Fig. 3 - On-State Power Loss Characteristics



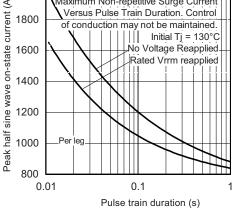


Fig. 6 - Maximum Non-Repetitive Surge Current

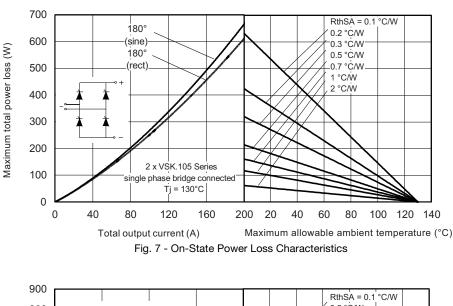
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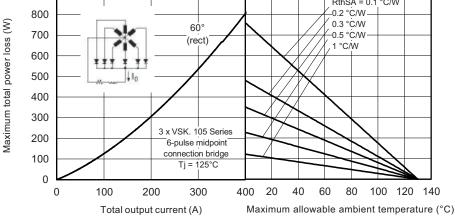
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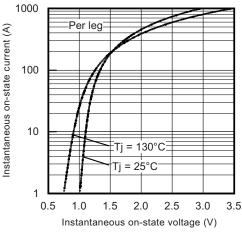
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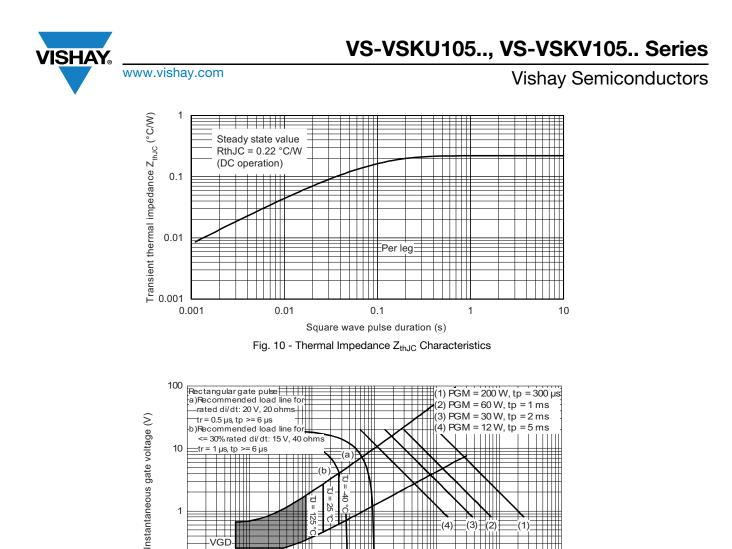
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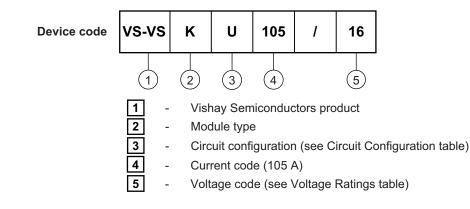
Frequency Limited by PG(AV

100

1000

ORDERING INFORMATION TABLE

0.1 0.001



VSK.105.. Series

1

Instantaneous gate current (A) Fig. 11 - Gate Characteristics

0.1

Note

To order the optional hardware go to www.vishay.com/doc?95172

VGD

IGD

0.01

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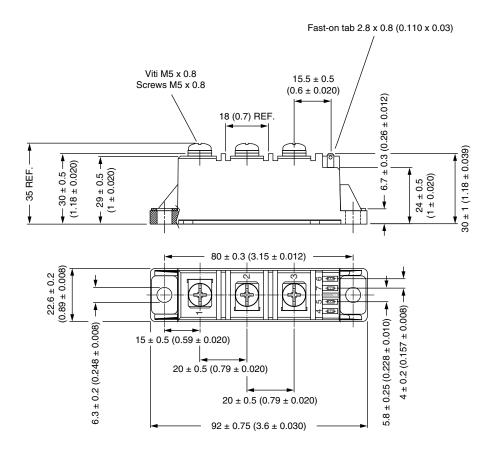
CIRCUIT CONFIGURATION								
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
Two SCRs common cathodes	U	VSKU 1 1 1 2 4 5 7 6 (1) - (2) (2) (2) (2) (3) (3) (3) (3) (3) (3) (4) (4) (4) (5) (7) (6)						
Two SCRs common anodes	V	VSKV (1) (1) (2) (2) (2) (2) (3) (3) (3) (3) (3) (3) (3) (3						
	LINKS TO RELATED D	OCUMENTS						
Dimensions		www.vishay.com/doc?95368						

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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)

SHA





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